NTD5806N, NVD5806N

Power MOSFET

40 V, 33 A, Single N−Channel, DPAK/IPAK

Features

- Low $R_{DS(on)}$
- High Current Capability
- Avalanche Energy Specified
- AEC−Q101 Qualified and PPAP Capable − NVD5806N
- These Devices are Pb−Free and are RoHS Compliant

Applications

- CCFL Backlight
- DC Motor Control
- Power Supply Secondary Side Synchronous Rectification

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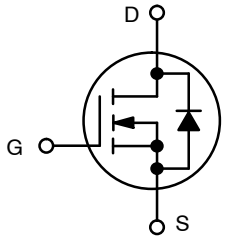
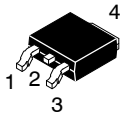
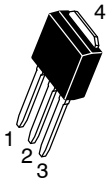
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
40 V	26 mΩ @ 4.5 V	33 A
	19 mΩ @ 10 V	



N−CHANNEL MOSFET



DPAK
CASE 369C
(Surface Mount)
STYLE 2



IPAK
CASE 369D
(Straight Lead DPAK)

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	40	V
Gate−to−Source Voltage − Continuous			V_{GS}	±20	V
Gate−to−Source Voltage − Non−Repetitive (t_p < 10 μS)			V_{GS}	±30	V
Continuous Drain Current ($R_{\theta JC}$) (Note 1)	Steady State	T_C = 25°C	I_D	33	A
		T_C = 100°C		23	
Power Dissipation ($R_{\theta JC}$) (Note 1)		T_C = 25°C	P_D	40	W
Pulsed Drain Current	t_p = 10 μs		I_{DM}	67	A
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to 175	°C
Source Current (Body Diode)			I_S	33	A
Single Pulse Drain−to−Source Avalanche Energy (V_{DD} = 50 V, V_{GS} = 10 V, R_G = 25 Ω, $I_{L(pk)}$ = 28 A, L = 0.1 mH, V_{DS} = 40 V)			E_{AS}	39	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

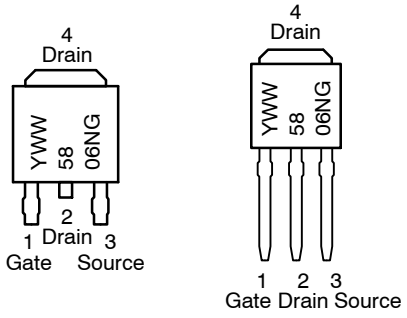
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Drain)	$R_{\theta JC}$	3.7	°C/W
Junction−to−Ambient − Steady State (Note 1)	$R_{\theta JA}$	57.5	

1. Surface−mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces.

MARKING DIAGRAMS & PIN ASSIGNMENT



Y = Year
WW = Work Week
5806N = Device Code
G = Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		40	45.5		V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				29.5		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 40 V	T_J = 25°C			1.0	μA
			T_J = 150°C			100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.4		2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				5.8		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 15 A			12.7	19	mΩ
		V_{GS} = 4.5 V, I_D = 10 A			17.8	26	
CHARGES, CAPACITANCES AND GATE RESISTANCES							
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 25 V			860		pF
Output Capacitance	C_{oss}				130		
Reverse Transfer Capacitance	C_{rss}				100		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 20 V, I_D = 30 A			17	38	nC
Threshold Gate Charge	$Q_{G(TH)}$				0.95		
Gate−to−Source Charge	Q_{GS}				3.4		
Gate−to−Drain Charge	Q_{GD}				4.5		
SWITCHING CHARACTERISTICS (Note 3)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 4.5 V, V_{DD} = 20 V, I_D = 30 A, R_G = 2.5 Ω			10.6		ns
Rise Time	t_r				93.7		
Turn−Off Delay Time	$t_{d(off)}$				14.2		
Fall Time	t_f				4.3		
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 10 V, V_{DD} = 20 V, I_D = 30 A, R_G = 2.5 Ω			8.0		ns
Rise Time	t_r				49		
Turn−Off Delay Time	$t_{d(off)}$				19.8		
Fall Time	t_f				2.6		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 10 A	T_J = 25°C		0.86	1.2	V
			T_J = 150°C		0.69		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dIs/dt = 100 A/μs, I_S = 30 A			18.8		ns
Charge Time	ta				11.8		
Discharge Time	tb				7.0		
Reverse Recovery Charge	Q_{RR}				10.9		nC

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CHARACTERISTICS

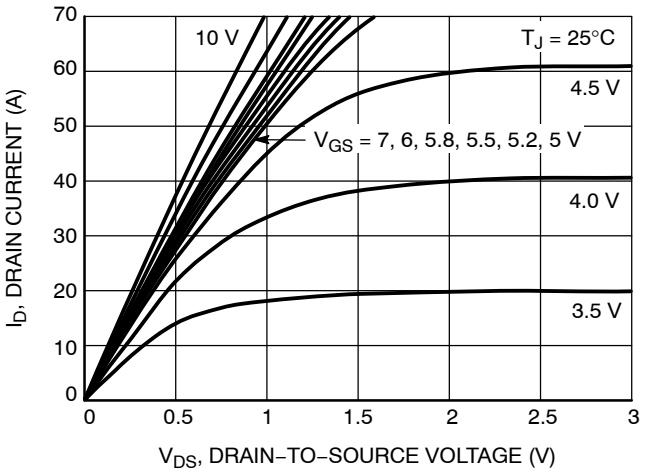


Figure 1. On−Region Characteristics

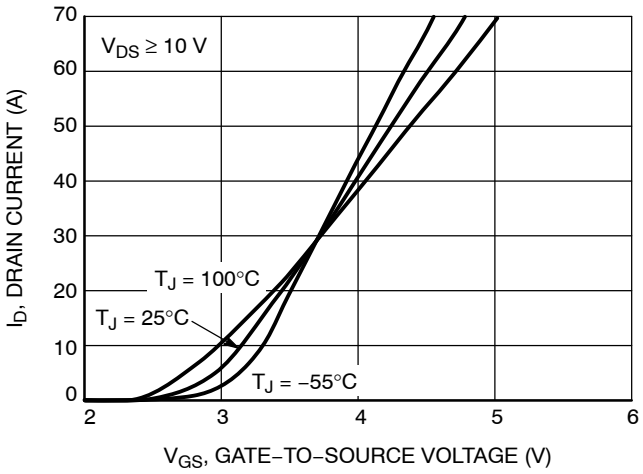


Figure 2. Transfer Characteristics

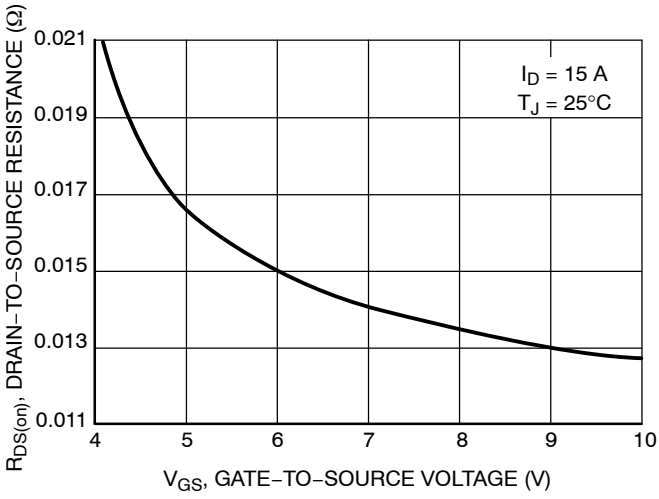


Figure 3. On−Resistance vs. Drain Current

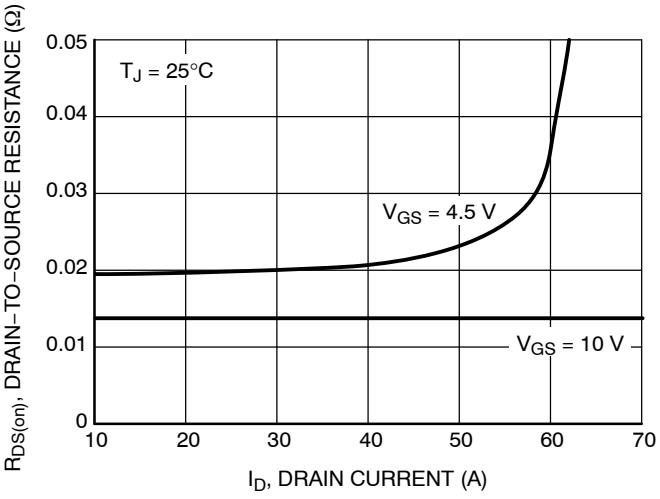


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

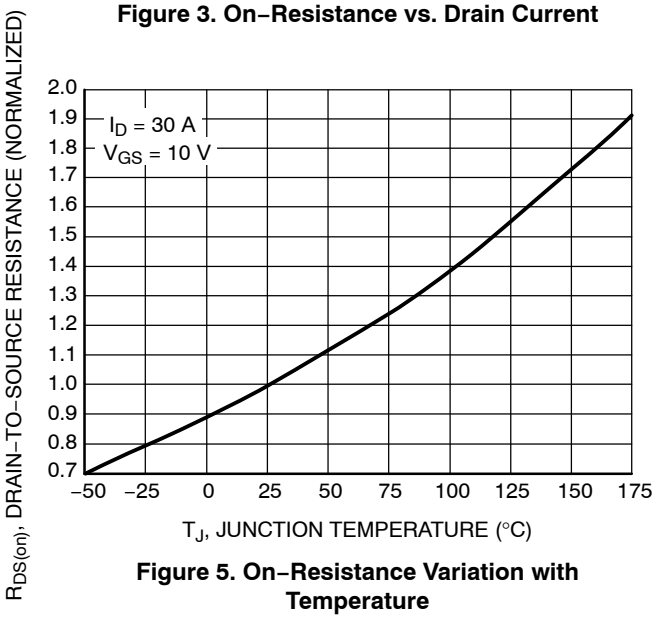


Figure 5. On−Resistance Variation with Temperature

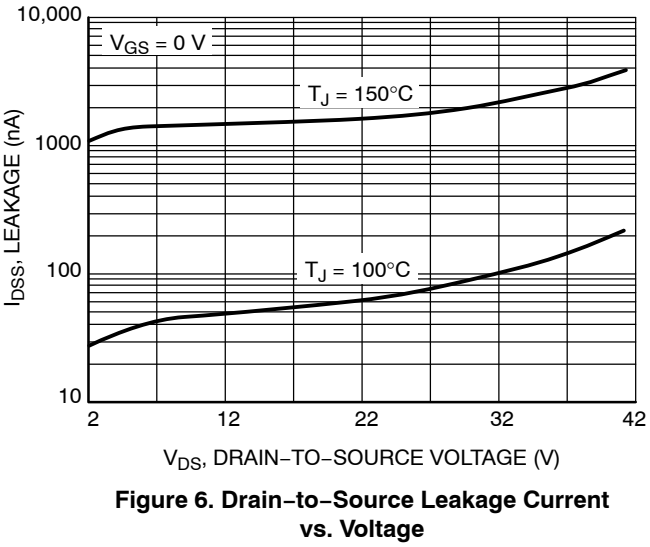


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CHARACTERISTICS

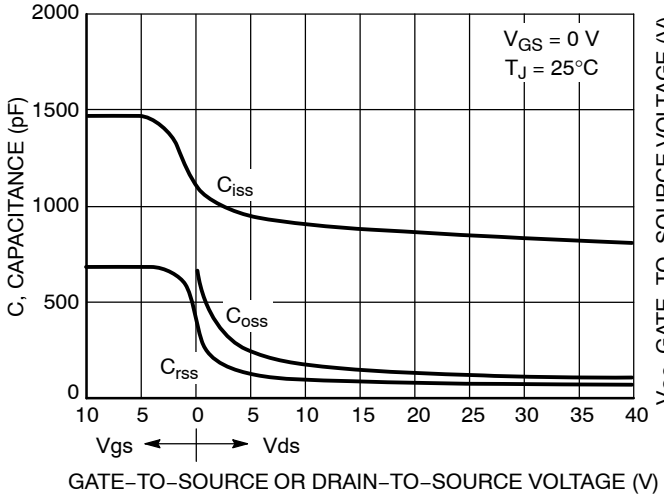


Figure 7. Capacitance Variation

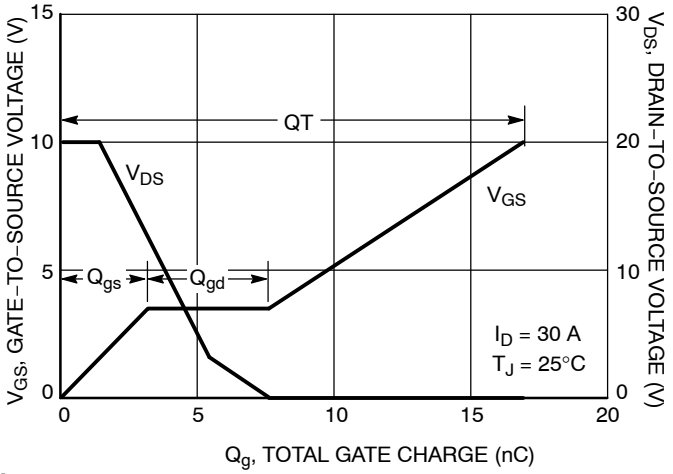


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

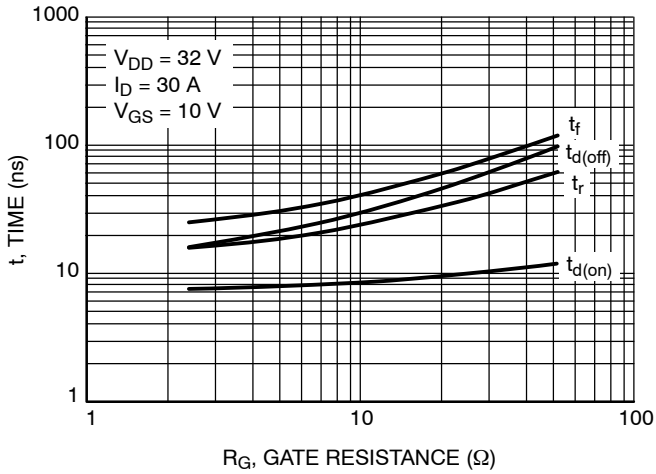


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

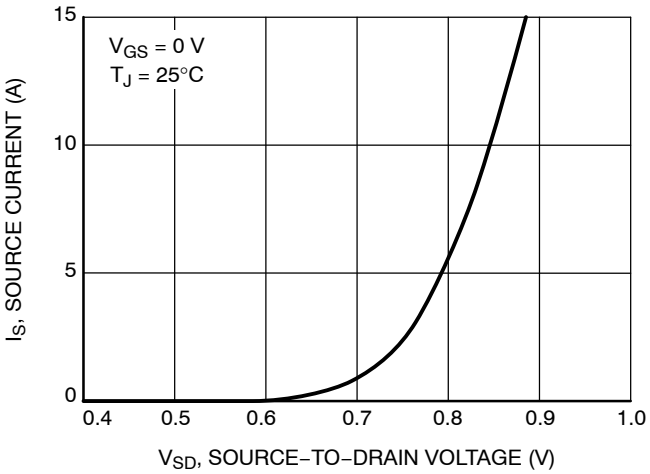


Figure 10. Diode Forward Voltage vs. Current

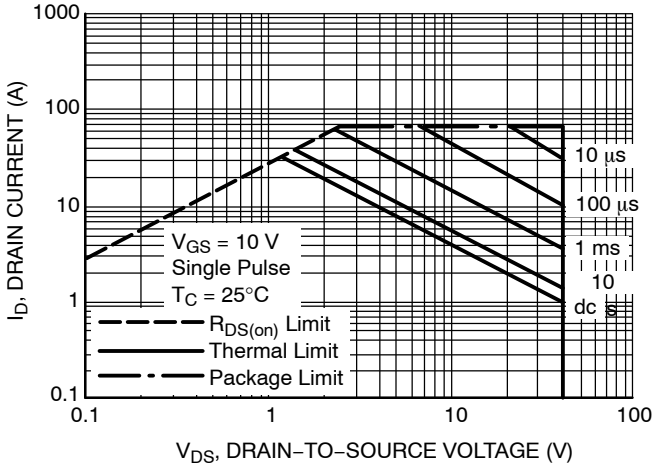


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL PERFORMANCE CHARACTERISTICS

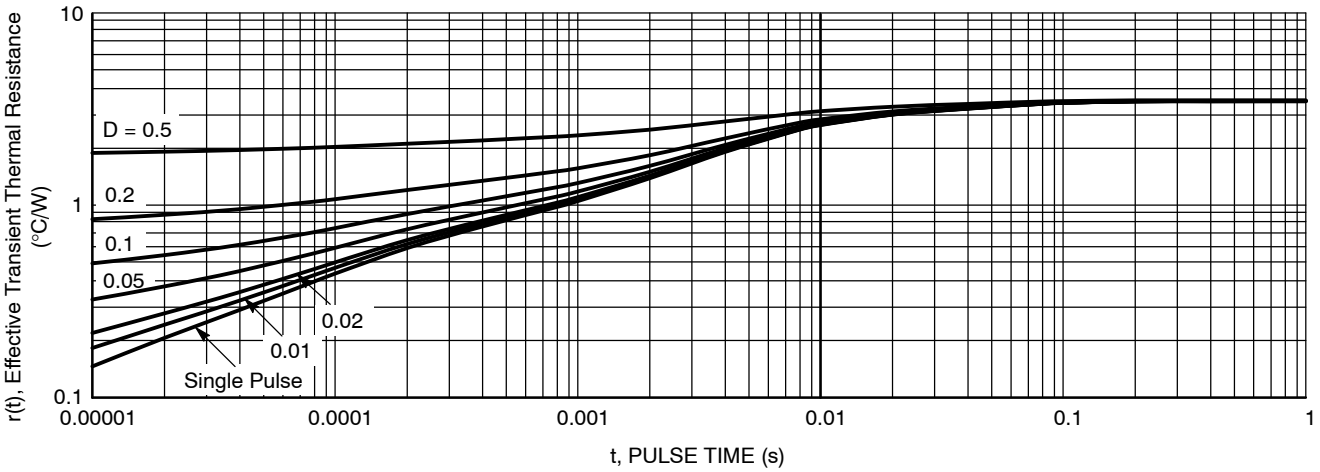


Figure 12. Thermal Response

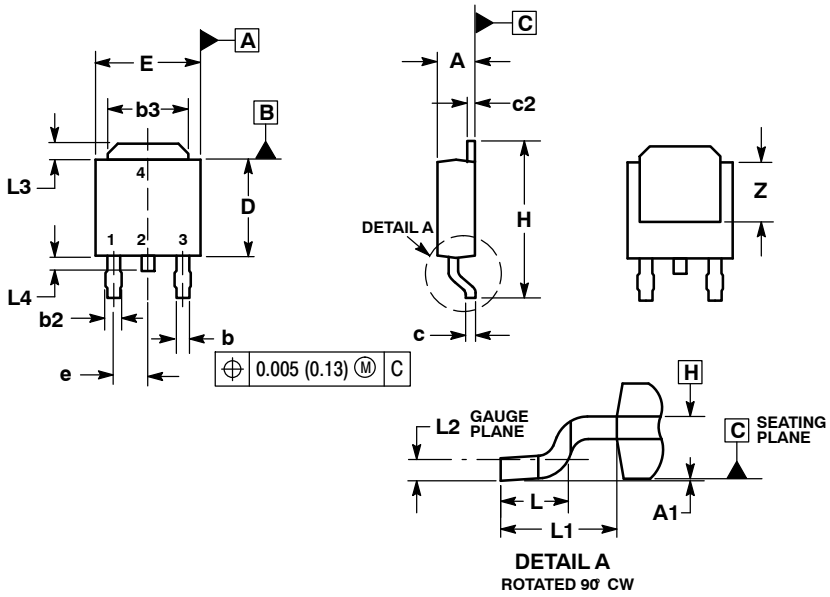
ORDERING INFORMATION

Order Number	Package	Shipping†
NTD5806NG	IPAK (Straight Lead DPAK) (Pb−Free)	75 Units / Rail
NTD5806NT4G	DPAK (Pb−Free)	2500 / Tape & Reel
NVD5806NT4G	DPAK (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

DPAK
CASE 369C−01
ISSUE D

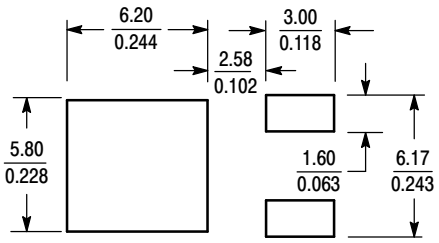


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	−−−	0.040	−−−	1.01
Z	0.155	−−−	3.93	−−−

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*

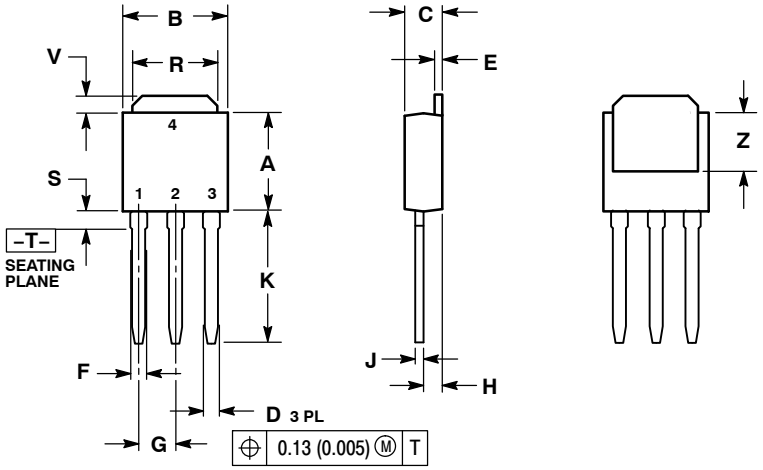


SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

IPAK
CASE 369D−01
ISSUE C



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	−−−	3.93	−−−

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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